

CORRECTION

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Correction: Ultrahigh power factor and flexible silver selenide-based composite film for thermoelectric devices

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Correction for 'Ultrahigh power factor and flexible silver selenide-based composite film for thermoelectric devices' by Yao Lu et al., *Energy Environ. Sci.*, 2020, DOI: 10.1039/c9ee01609k.

Following publication of this article the authors noted that the thickness of the films, which affects the electrical conductivity, is affected by the synthesis temperature of the silver selenide-based nanowires. When the experiments were repeated the room temperature was around 10 °C higher than when the original experiments were performed and this may influence the quality of the synthesized nanowires and finally the properties of the films.

The experiments have been redone in order to obtain repeatable data which differs slightly to that published in the original article. The authors wish to replace Fig. 2, 4 and S4 with new figures as follows. This correction does not affect any other data or change any of the scientific conclusions in the article.

Fig. 2 should be replaced by:

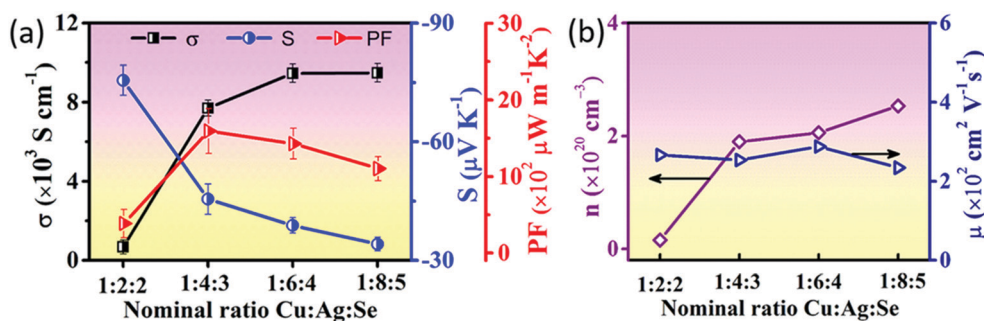


Fig. 2 Room temperature TE parameters (a), carrier concentration and mobility (b) of the $\text{Cu}_x\text{Ag}_y\text{Se}_z$ films starting from different Cu/Ag/Se nominal molar ratios.

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Fig. 4 should be replaced by:

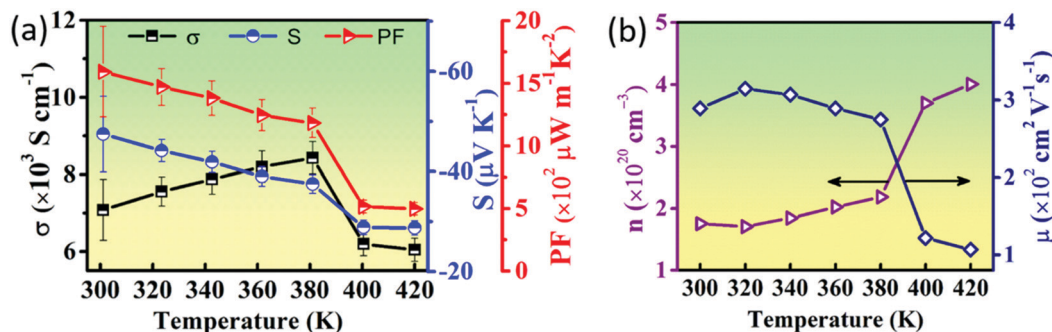


Fig. 4 Temperature dependence of the TE parameters (a), carrier concentration and mobility (b) for the Cu₁Ag₄Se₃ film.

Supplementary Fig. S4 should be replaced by:

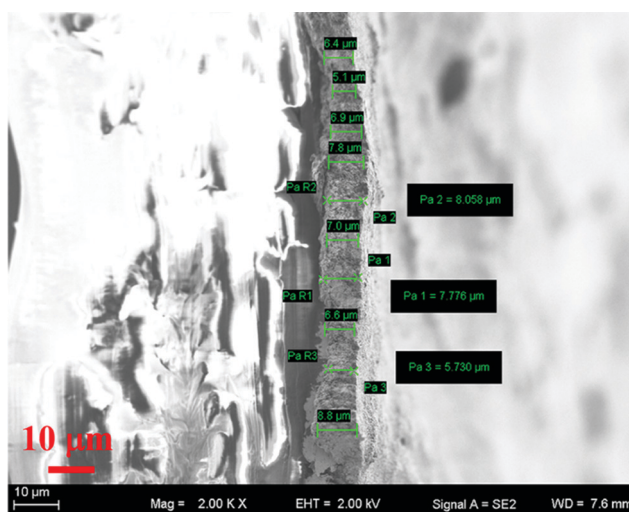


Fig. S4 A typical fractured surface SEM image of the composite films.

The authors also wish to replace the data related to Fig. 2, 4 and S4 in the manuscript. For example, “2231.5 $\mu\text{W m}^{-1} \text{ K}^{-2}$,” should read as “1593.9 $\mu\text{W m}^{-1} \text{ K}^{-2}$,” and “ $zT \sim 0.5$ at 300 K” should read as “ $zT \sim 0.4$ at 300 K”.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

